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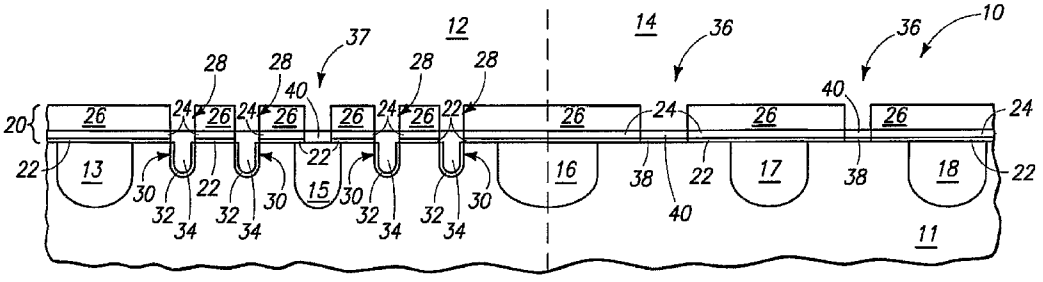
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(54) Title: METHOD OF FORMING FIELD EFFECT TRANSISTORS AND METHODS OF FORMING INTEGRATED CIRCUITY COMPRISING A TRANSISTOR GATE ARRAY AND CIRCUITY PERIPHERAL TO THE GATE ARRAY



(57) Abstract: The invention includes methods of forming field effect transistors, methods of forming field effect transistor gates, methods of forming integrated circuitry- comprising a transistor gate array and circuitry peripheral to the gate array, and methods of forming integrated circuitry comprising a transistor gate array including first gates and second grounded isolation gates. In one implementation, a method of forming a field effect transistor includes forming masking material (22, 24, 26) over semiconductive material of a substrate (11). A trench (30) is formed through the masking material (22, 24, 26) and into the semiconductive material (11). Gate dielectric material (32) is formed within the trench (30) in the semiconductive material (11). Gate material (34) is deposited within the trench (30) in the masking material (22, 24, 26) and within the trench (30) in the semiconductive material (11) over the gate dielectric material (32). Source/drain regions are formed. Other aspects and implementations are contemplated.

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